

BUK964R7-80E

N-channel TrenchMOS logic level FET

13 March 2014

Product data sheet

1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

3. Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V	
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	324	W	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	3.6	4.7	mΩ	
Dynamic characteristics								
Q_{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 64 V; Fig. 13; Fig. 14		-	28.9	-	nC	

[1] Continuous current is limited by package.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G—VIII
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK964R7-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK964R7-80E	BUK964R7-80E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	80	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
		T _j ≤ 175 °C; DC		-10	10	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	324	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	120	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	120	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	667	Α
T _{stg}	storage temperature			-55	175	°C

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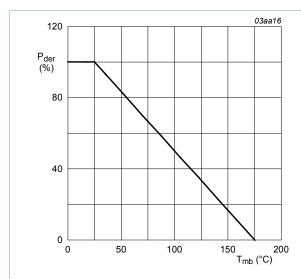
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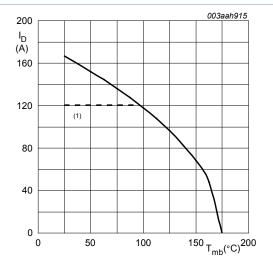
Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drain	diode					_
I _S	source current	T _{mb} = 25 °C	[3]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	667	Α
Avalanche ru	ggedness		'			_
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 120 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[4][5]	-	384	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Continuous current is limited by package.
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. Refer to application note AN10273 for further information.



Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times 100 \%$$



(1) Capped at 120A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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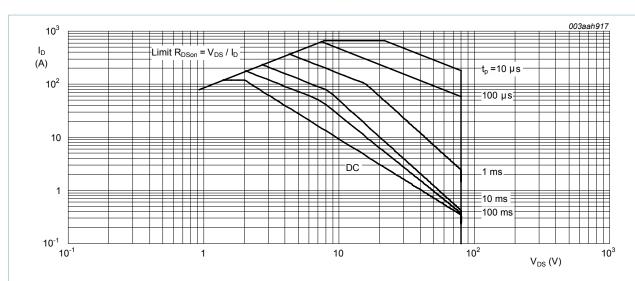


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



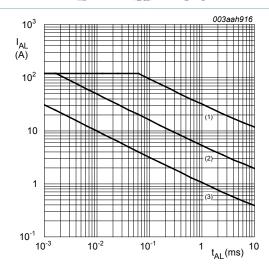


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (int)} = 25^{\circ}C$; (2) $T_{j (int)} = 150^{\circ}C$; (3) Repetitive Avalanche

9. Thermal characteristics

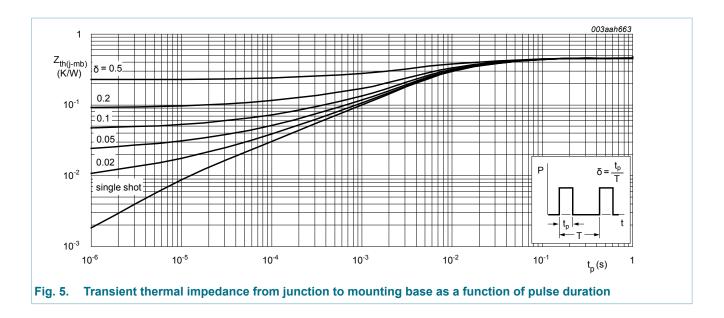
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.46	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	80	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.13	1	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	3.6	4.7	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	3.3	4.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	11.7	mΩ
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 64 V; V _{GS} = 5 V;	-	92.1	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	25.7	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{GD}	gate-drain charge		-	28.9	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	11500	15340	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	744	892	pF
C _{rss}	reverse transfer capacitance		-	360	493	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R_L = 2.4 Ω ; V_{GS} = 5 V;	-	54.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	95.7	-	ns
t _{d(off)}	turn-off delay time		-	112	-	ns
t _f	fall time		-	82.3	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nΗ
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode				'	,
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	49.8	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	97.2	-	nC

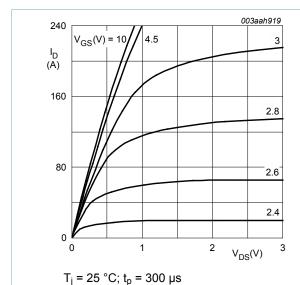


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

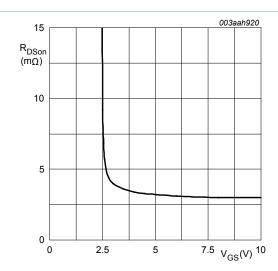


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

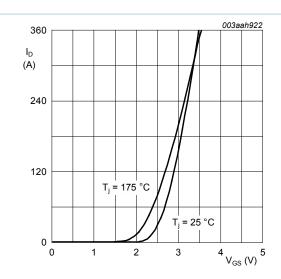


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



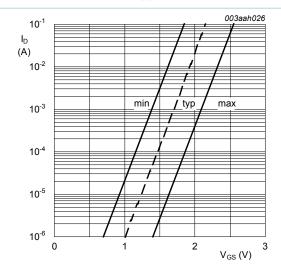


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

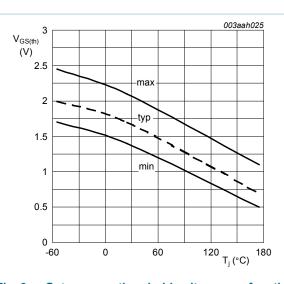
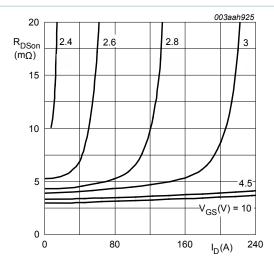


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1$$
 mA; $V_{DS} = V_{GS}$



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

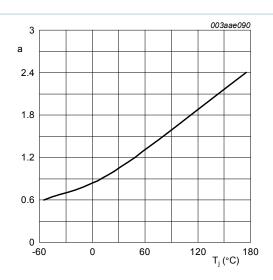


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

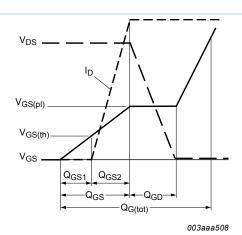


Fig. 13. Gate charge waveform definitions

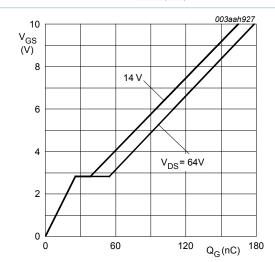


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

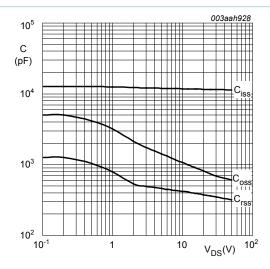


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

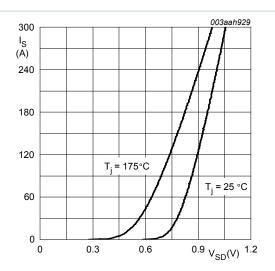
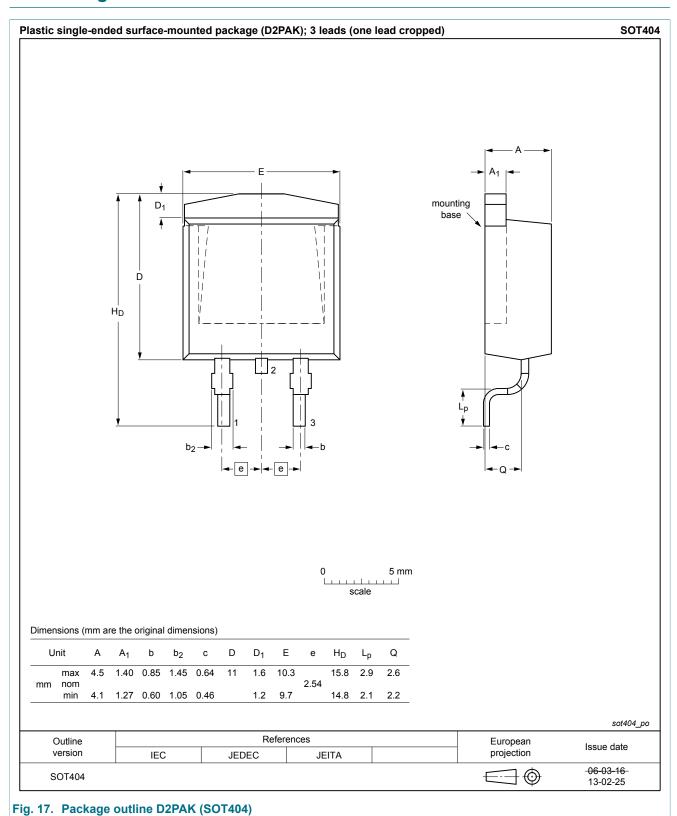


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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